

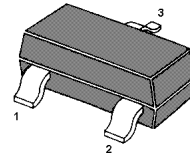
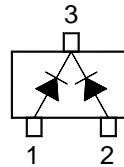
# 1SS392

## SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low voltage high speed switching application

### Features

- Low forward voltage
- Low reverse current



Marking Code: "ZD"  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	40	V
Average Forward Current	$I_O$	100	mA
Maximum Peak Forward Current	$I_{FM}$	300	mA
Non-Repetitive Peak Forward Surge Current ( $t = 10\text{ ms}$ )	$I_{FSM}$	1	A
Power Dissipation	$P_d$	150	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	-	0.6	V
Reverse Current at $V_R = 40\text{ V}$	$I_R$	-	5	$\mu\text{A}$
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	45	-	V
Total Capacitance at $V_R = 0$ , $f = 1\text{ MHz}$	$C_T$	-	25	pF

